

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0006] of Applicant's published application as follows:

[0006] In the meantime, a GaN-based nitride semiconductor light emitting device is mainly grown-up on a substrate 2000. The substrate 2000 may be a sapphire substrate or a SiC substrate. Additionally, a GaN-based polycrystalline layer is grown-up as a buffer layer on the sapphire substrate or the SiC substrate at a low growing-up temperature, and then a first conductive layer 2001 (e.g., an undoped GaN layer, a silicon (Si) doped N-type GaN layer, or an N-type GaN-based layer having a combination structure thereof) is formed on the buffer layer at a high temperature. After that, a light emitting layer (quantum-well-structured active layer 2002) is formed on the first conductive layer 2001 (e.g., the N-type GaN-based layer), and a P-type GaN-based layer is additionally formed on the light emitting layer such that the semiconductor light emitting device is manufactured.